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10/718,640	11/24/2003	Koji Shigemura	1670.1019	1164
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EXAMINER WALFORD, NATALIE K				
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**Please find below and/or attached an Office communication concerning this application or proceeding.**

The time period for reply, if any, is set in the attached communication.

# Office Action Summary

**Application No.**

10/718,640

**Applicant(s)**

SHIGEMURA ET AL.

**Examiner**

NATALIE K. WALFORD

**Art Unit**

2879

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --  
**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 28 January 2008.  
2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.  
3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 1-41 and 49-56 is/are pending in the application.  
4a) Of the above claim(s) 7-9, 24, 25, 31-33 and 39-41 is/are withdrawn from consideration.  
5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.  
6) ☒ Claim(s) 1-6, 10-23, 26-30, 34-38 and 49-56 is/are rejected.  
7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.  
8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.  
10) ☒ The drawing(s) filed on 24 November 2003 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

**Priority under 35 U.S.C. § 119**

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a) ☒ All b) ☐ Some \* c) ☐ None of:  
1. ☒ Certified copies of the priority documents have been received.  
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

**Attachment(s)**

- 1) ☐ Notice of References Cited (PTO-892)  
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)  
3) ☒ Information Disclosure Statement(s) (PTO/SB/08)  
Paper No(s)/Mail Date 2/08  
4) ☐ Interview Summary (PTO-413)  
Paper No(s)/Mail Date \_\_\_\_\_  
5) ☐ Notice of Informal Patent Application  
6) ☐ Other: \_\_\_\_\_

**DETAILED ACTION**

***Response to Amendment***

The Response, filed on January 28, 2008 has been entered and acknowledged by the Examiner. Claims 1-41 and 49-56 are pending in the instant application.

***Claim Rejections - 35 USC § 102***

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-2, 4-5, 10, 12-13, 15, 17-18, 20-21, 23, 26, 28-29, 34, 36-37, 49-56 are rejected under 35 U.S.C. 102(b) as being anticipated by Yokoi et al. (JP 2000-160323).

Regarding claim 1, Yokoi discloses an evaporation mask in figure 10 formed of a thin film (item 3), wherein the evaporation mask is drawn taut by application of tension (paragraph 5) and comprises: at least one mask unit (item 3), comprising: a plurality of main apertures (item 4), and a plurality of first dummy apertures (item 4) formed adjacent to outermost ones of the main apertures in a direction in which tension is applied to the evaporation mask.

Regarding claim 2, Yokoi discloses the evaporation mask of claim 1, wherein the main apertures form an effective deposition area (see FIG. 10), and the first dummy apertures form an ineffective deposition area (see FIG. 10).

Regarding claim 4, Yokoi discloses the evaporation mask of claim 2, comprising at least two mask units (item 3), and further comprising a plurality of second dummy apertures (item 4)

formed outside and adjacent to the outermost mask units in the direction in which tension is applied to the evaporation mask (paragraph 5).

Regarding claim 5, Yokoi discloses the evaporation mask of claim 4, wherein the second dummy apertures are formed outside the effective deposition areas where the mask units are formed (see FIG. 10).

Regarding claim 10, Yokoi discloses a method of manufacturing an organic electroluminescent (EL) device in figures 10 and 16, the method comprising: forming first electrodes (item 60) on a substrate (item 6); disposing an evaporation mask (item 3) to form an organic film over the substrate (item 61), the evaporation mask drawn taut by application of tension (paragraph 5) and having at least one mask unit (item 3), the mask unit comprising a plurality of main apertures (item 4) and a plurality of first dummy apertures (item 4) formed adjacent to outermost ones of the main apertures in a direction in which tension is applied to the evaporation mask; forming the organic film comprising an effective luminescent area to cover at least the first electrodes by evaporating an organic material containing an organic luminescent material through the main apertures (see FIG. 16), and forming a first dummy pattern area (area around item 4) outside the effective luminescent area through the first dummy apertures; forming second electrodes on the organic film (item 52) so that the effective luminescent area is formed at an area where the first and second electrodes overlap; and sealing the resulting structure (see FIG. 16).

Regarding claim 12, Yokoi discloses the method of claim 10, wherein at least two organic EL devices are manufactured in a single process (see FIG. 14), and the evaporation mask comprises at least two mask units (item 3), through each of which the organic film of a single

organic EL device can be deposited, and a plurality of second dummy apertures (item 4) outside and adjacent to outermost ones of the mask units in the direction in which tension is applied to the evaporation mask (paragraph 5).

Regarding claim 13, Yokoi discloses the method of claim 12, wherein the second dummy apertures of the evaporation mask are located outside the effective luminescent areas of the organic EL devices that are deposited by the outermost mask units adjacent to the second dummy apertures (see FIG. 10).

Regarding claim 15, Yokoi discloses the method of claim 10, wherein in forming the second electrodes, an evaporation mask (item 3) to form the second electrodes is disposed over the substrate, the evaporation mask drawn taut by application of tension (paragraph 5) and having at least one mask unit (item 3), the mask unit comprising a plurality of main apertures (item 4) and a plurality of first dummy apertures (item 4) formed adjacent to the outermost main apertures in the direction in which tension is applied to the evaporation mask, the second electrodes are formed on the effective luminescent area through the main apertures (see FIG. 16), and a second dummy pattern area is formed outside the effective luminescent area through the first dummy apertures (see FIG. 16).

Regarding claim 17, Yokoi discloses the method of claim 15, wherein at least two organic EL devices are manufactured in a single process, and the evaporation mask comprises at least two mask units (item 3), through each of which the second electrodes (item 52) of a single organic EL device can be deposited, and a plurality of second dummy apertures (item 4) outside and adjacent to the outermost mask units in the direction in which tension is applied to the evaporation mask (paragraph 5).

Regarding claim 18, Yokoi discloses the method of claim 17, wherein the second dummy apertures are located outside the effective luminescent areas of the organic EL devices that are deposited by the outermost mask units adjacent to the second dummy apertures (see FIG. 10).

Regarding claim 20, Yokoi discloses the method of claim 10, wherein at least two organic EL devices are manufactured in a single process, the second electrodes (item 52) are formed using an evaporation mask (item 3) drawn taut by application of tension (paragraph 5) and having at least two mask units (item 3), through which the second electrodes of the organic EL devices can be deposited, and the evaporation mask comprises a plurality of second dummy apertures (item 4) outside and adjacent to outermost mask units in the direction in which tension is applied to the evaporation mask (paragraph 5).

Regarding claim 21, Yokoi discloses the method of claim 20, wherein the second dummy apertures are located outside the effective luminescent areas of the organic EL devices that are deposited by the outermost mask units adjacent to the second dummy apertures (see FIG. 10).

Regarding claim 23, Yokoi discloses a method of manufacturing an organic EL device in figures 10 and 16, the method comprising: forming first electrodes (item 60) for an organic EL device on a substrate (item 6); disposing an evaporation mask (item 3) to form an organic film (item 61) over the substrate, the evaporation mask drawn taut by application of tension (paragraph 5) and including at least two mask units (item 3) each comprising a plurality of main apertures (item 4) and a plurality of second dummy apertures (item 4) formed outside and adjacent to outermost ones of the mask units in a direction in which tension is applied to the evaporation mask (paragraph 5); forming the organic film (item 61) comprising an effective luminescent area to cover at least the first electrodes by evaporating an organic material

containing an organic luminescent material through the main apertures of each of the mask units (see FIG. 10); forming second electrodes (item 52) on the organic film so that the effective luminescent area is formed at an area where the first and second electrodes overlap; and scaling the resulting structure (see FIG. 16).

Regarding claim 26, Yokoi discloses the method of claim 23, wherein in forming the second electrodes, an evaporation mask (item 3) to form the second electrodes (item 52) is disposed over the substrate (item 6), the evaporation mask drawn taut by application of tension (paragraph 5) and including at least two mask units (item 3), the mask units each comprising a plurality of main apertures (item 4) and a plurality of first dummy apertures (item 4) formed adjacent to the outermost main apertures in the direction in which tension is applied to the evaporation mask, the second electrodes are formed on each of the effective luminescent areas through the main apertures (see FIG. 10), and a second dummy pattern area is formed outside each of the effective luminescent areas through the first dummy apertures (see FIG. 10).

Regarding claim 28, Yokoi discloses the method of claim 26, wherein the evaporation mask comprises a plurality of second dummy apertures (item 4) outside and adjacent to the outermost mask units in the direction in which tension is applied to the evaporation mask.

Regarding claim 29, Yokoi discloses the method of claim 28, wherein the second dummy apertures of the evaporation mask are located outside the effective luminescent areas of the organic EL devices that are deposited by the outermost mask units adjacent to the second dummy apertures (see FIG. 10).

Regarding claim 34, Yokoi discloses a method of manufacturing an organic EL device in figures 10 and 16, the method comprising: forming first electrodes (item 60) on a substrate (item

6) in a predetermined pattern; forming an organic film (item 61) comprising an effective luminescent area to cover at least the first electrodes by evaporating an organic material containing an organic luminescent material (item 61); disposing an evaporation mask (item 3) to form second electrodes over the organic film, the evaporation mask drawn taut by application of tension (paragraph 5) and comprising a plurality of main apertures (item 4) and a plurality of first dummy apertures (item 4) formed adjacent to outermost ones of the main apertures in a direction in which tension is applied to the evaporation mask; forming the second electrodes (item 52) through the main apertures so that the effective luminescent area is formed at an area where the first and second electrodes overlap (see FIG. 16), and forming a second dummy pattern area (area around item 4) outside the effective luminescent area through the first dummy apertures; and sealing the resulting structure (see FIG. 16).

Regarding claim 36, Yokoi discloses the method of claim 34, wherein at least two organic EL devices are manufactured in a single process, and the evaporation mask (item 3) comprises at least two mask units (item 3), through each of which the second electrodes (item 52) of a single organic EL device can be deposited, and a plurality of second dummy apertures (item 4) outside and adjacent to outermost ones of the mask units in the direction in which tension is applied to the evaporation mask (paragraph 5).

Regarding claim 37, Yokoi discloses the method of claim 36, wherein the second dummy apertures of the evaporation mask are located outside the effective luminescent areas of the organic EL devices that are deposited by the outermost mask units adjacent to the second dummy apertures (see FIG. 10).



Regarding claim 49, Yokoi discloses an evaporation mask in figure 10 formed of a thin film (item 3), wherein the evaporation mask is drawn taut by application of tension (paragraph 5), the evaporation mask comprising: at least one mask unit (item 3) comprising: at least one main aperture (item 4), and at least one first dummy aperture (item 4) formed adjacent to an outermost at least one main aperture in a direction in which tension is applied to the evaporation mask (paragraph 5).

Regarding claim 50, Yokoi discloses the evaporation mask of claim 49, further comprising at least one second dummy aperture (item 4) formed outside and adjacent to the outermost at least one mask unit in the direction in which tension is applied to the evaporation mask.

Regarding claim 51, Yokoi discloses a mask unit (item 3) for an evaporation mask in figure 10, comprising: a main aperture (item 4); and a dummy aperture (item 4); wherein the dummy aperture prevents the main aperture from being deformed by tension applied to the evaporation mask (paragraph 5).

Regarding claim 52, Yokoi discloses the evaporation mask of claim 1, wherein a length of each of the first dummy apertures is equal to a length of each of the main apertures (see FIG. 10).

Regarding claim 53, Yokoi discloses the method of claim 10, wherein a length of each of the first dummy apertures is equal to a length of each of the main apertures (see FIG. 10).

Regarding claim 54, Yokoi discloses the method of claim 34, wherein a length of each of the first dummy apertures is equal to a length of each of the main apertures (see FIG. 10).

Regarding claim 55, Yokoi discloses the evaporation mask of claim 49, wherein a length of each of the at least one first dummy aperture is equal to a length of each of the at least one main aperture (see FIG. 10).

Regarding claim 56, Yokoi discloses the mask unit of claim 51, wherein a length of the dummy aperture is equal to a length of the main aperture (see FIG. 10).

***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 3, 6, 11, 14, 16, 19, 22, 27, 30, 35, and 38 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yokoi et al. (JP 2000-160323) in view of Himeshima et al. (US 6,469,439).

Regarding claim 3, Yokoi discloses the evaporation mask of claim 2, but does not expressly disclose that at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at

least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 6, Yokoi discloses the evaporation mask of claim 4, but does not expressly disclose that at least one of the second dummy apertures is formed parallel to the main apertures of the mask units, and at least another one of the second dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 11, Yokoi discloses the method of claim 10, but does not expressly disclose that at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at

least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 14, Yokoi discloses the method of claim 12, but does not expressly disclose that at least one of the second dummy apertures is formed parallel to the main apertures of the mask units, and at least another one of the second dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 16, Yokoi discloses the method of claim 15, but does not expressly disclose that at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main

apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 19, Yokoi discloses the method of claim 17, but does not expressly disclose that at least one of the second dummy apertures is formed parallel to the main apertures of the mask units, and at least another one of the second dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 22, Yokoi discloses the method of claim 20, but does not expressly disclose that at least one of the second dummy apertures is formed parallel to the main apertures of the mask units, and at least another one of the second dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main

apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 27, Yokoi discloses the method of claim 26, but does not expressly disclose that at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 30, Yokoi discloses the method of claim 28, but does not expressly disclose that at least one of the second dummy apertures is formed parallel to the main apertures of the mask units, and at least another one of the second dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an

evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 35, Yokoi discloses the method of claim 34, but does not expressly disclose that at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

Regarding claim 38, Yokoi discloses the method of claim 36, but does not expressly disclose that at least one of the second dummy apertures is formed parallel to the main apertures of the mask units, and at least another one of the second dummy apertures is formed

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perpendicular to the main apertures, as claimed by Applicant. Himeshima is cited to show an evaporation mask in figure 35 with first dummy apertures (item 32) formed parallel to the main apertures (item 32), and at least another one of the first dummy apertures (item 32) is formed perpendicular to the main apertures (item 32). It would have been obvious to one having ordinary skill in the art to have at least one of the first dummy apertures is formed parallel to the main apertures, and at least another one of the first dummy apertures is formed perpendicular to the main apertures, since such a modification would have involved a mere change in the shape of a component. A change in shape is generally recognized as being within the level of ordinary skill in the art.

### ***Response to Arguments***

Applicant's arguments with respect to claims 1-41 and 49-56 have been considered but are moot in view of the new ground(s) of rejection.

### ***Contact Information***

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Natalie K. Walford whose telephone number is (571)-272-6012. The examiner can normally be reached on Monday-Friday, 8 AM - 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nimesh Patel can be reached on (571)-272-2457. The fax phone number for the organization where this application or proceeding is assigned is (571)-273-8300.



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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Nkw

/Natalie K Walford/

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